

Spin-transfer Magnetization Switching in CPP-GMR Films with Half-metallic Co₂MnSi

S. Murakami¹, Y. Sakuraba¹, H. Kubota², M. Oogane¹, Y. Ando^{1*}, and T. Miyazaki¹

¹ Graduate School of Engineering, Tohoku University, Aoba-yama, Sendai 980-8579, Japan
² National Institute of Advanced Industrial Science and Technology, 1-1-1 Umezono, Tsukuba 305-8568, Japan
 *Corresponding author: ando@mrlab.aiph.tohoku.ac.jp, Phone: +81 22 795 7949, Fax: +81 22 795 7947

The perfect spin polarized materials, which called half-metallic ferromagnets (HMFs), have been greatly important in spin electronic devices because these materials have a possibility to improve MR ratio on GMR or tunnelling magnetoresistance (TMR) junctions. Half-metallic property in full-Heusler alloys such as Co₂MnSi and Co₂MnGe was theoretically predicted by some groups. As some experimentally results, Heusler alloys indicated high TMR ratio which suggest the potential of HMFs. In the case of Co₂MnSi, it has been observed an extremely large TMR ratio at low temperature by Sakuraba et al. 1) In this work, we report spin-transfer magnetization switching in current-perpendicular-to-plane giant magnetoresistance (CPP-GMR) with a stacking of Co₂MnSi (30 nm)/Cu (6 nm)/Co₃Fe₂S (5 nm). The Co₂MnSi which is half-metallic Heusler alloy is used as a source of highly spin-polarized current.

X-ray diffraction pattern (XRD) of MgO substrate/Cr (40 nm)/Co₂MnSi (30 nm) showed the Co₂MnSi (200) and (400) peaks, indicating perfect (100)-oriented growth of Co₂MnSi. Also the pole-figure of the A2 (220) showed four fold symmetries, indicating that Co₂MnSi was epitaxially grown. The magnetoresistance ratio of the CPP-GMR film was 1.2%. Fig. 1 shows the pulsed currents duration dependence of switching current I_c plotted as a function of $\ln(\tau_p/\tau_0)$, where τ_p is the pulsed current duration, τ_0 is the attempt frequency. Consistent with other reports, the I_c gradually increase with decreasing the pulsed currents duration. The estimated $J_{c0}^{AP \rightarrow P}$ was -6.3×10^6 A/cm², and $J_{c0}^{P \rightarrow AP}$ was 8.7×10^6 A/cm² (7.5×10^6 A/cm² in average). The observed critical current density is the smallest value compare to those reported for CPP-GMR elements so far. In AP \rightarrow P transition, the critical switching current density J_{c0} for the sample with the Co₂MnSi-spin-filter was about 1/6 of that for the sample with CoFe-spin-filter. If the spin-polarization P changes from 0.50 to 0.75, the J_{c0} is expected to be about 1/6 using Slonczewski model²⁾. This result indicates that the reduction of the switching current density in CPP-GMR with Co₂MnSi electrode is due to increase of the spin-polarization of the spin-filter layer, suggesting that Co₂MnSi has a great advantage to reduce the switching current.

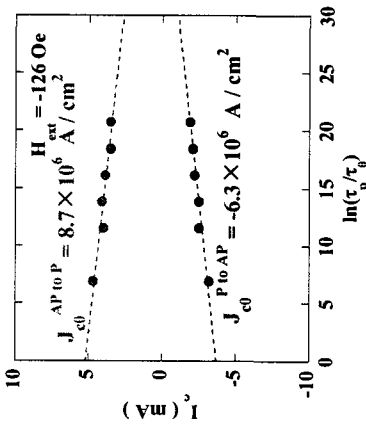


Fig. 1. The pulse duration dependence of I_c . Dashed lines are the results of a least-square fit.

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Spin Dependent Scattering of Nonequilibrium Holes in Co

B.G. Park^{1,2}, R. Jansen¹, and J. C. Lodder¹

¹ MESA+ Institute of Nanotechnology, University of Twente, 7500 AE Enschede, The Netherlands
² Hitachi Cambridge Laboratory, Cambridge CB3 0HE, United Kingdom

*Corresponding author: bp2866@cam.ac.uk, Phone: +44 1223 467 944, Fax: +44 1223 467 942

Spin-dependent scattering of electrons in a ferromagnet is essential to the understanding and application of various magnetic systems. The spin-dependent transport involves not only electrons at the Fermi level (EF) but in many cases also nonequilibrium (hot) carriers. One example is the magnetic tunnel junction which exhibits a large tunnel magnetoresistance (TMR) at low bias where electrons near EF are of relevance, while the TMR drops significantly at higher bias where states away from EF also participate in the tunneling process. The transmission of hot electrons injected into the empty states above EF of FM layers has been extensively studied, which shows the FM layers preferentially transmit hot electrons in the majority spin bands, leading to a spin filtering of hot electrons in a FM layer. On the other hand, the spin-dependent transport of carriers below EF (hot holes) is not well understood.

Here, we present on the spin-dependent transmission of holes injected into a ferromagnetic Co using a p-type magnetic tunnel transistor (p-MTT), which combines a magnetic tunnel junction and a p-type semiconductor. In a p-MTT, spin-polarized holes are injected into the states below EF of the FM base by a tunneling and they are collected in the valence band of the p-type semiconductor after spin-dependent transmission through the FM base. The magnetic response of the p-MTT device, so-called magnetocurrent (MC) is determined by the spin-dependent tunneling from the emitter, as well as spin-dependent scattering of the holes in the base. MTT's of p-type Si/Au(8nm)/Co/Al₂O₃(2nm)/NiFe(5nm) were deposited by e-beam evaporation in a molecular beam epitaxy system and patterned by standard photolithography. The MC and the transfer ratio have been studied as a function of Co base thickness and tunnel bias voltage applied to the emitter. For a p-MTT with large Co base thickness and/or large emitter bias, the MC has the usual positive sign. Thus, the transmission of holes in the majority spin band of Co is larger than that of minority spin holes. Surprisingly, for smaller Co thickness and bias near the collection threshold (0.3 eV), the MC reverses sign and becomes negative. Moreover, the hole transmission decays exponentially not with a single attenuation length but with two different attenuation lengths in the low and high thickness regime, respectively. The results are explained in terms of a competition of two scattering contributions, elastic and inelastic, with opposite spin asymmetry. Up to a critical thickness of about 3nm, (quasi)elastic scattering dominates with a short attenuation length (less than 1nm) and preferential attenuation of holes in the majority spin bands, consistent with spin-wave emission. At a larger Co thickness, inelastic scattering dominates with a larger attenuation length (~4nm) and opposite spin asymmetry.